

PNP Germanium UHF Transistor

AF 279 S

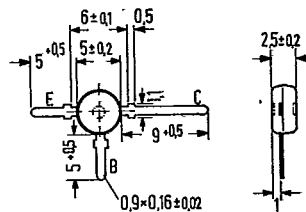
SIEMENS AKTIENGESELLSCHAFT 25C 04079 D _____

T-31-07

for input stages up to 900 MHz

AF 279 S is a germanium PNP UHF planar transistor with passivated surface in low-capacitance 50 B 3 DIN 41867 plastic package similar to TO 119. This transistor is particularly intended for use in low-noise regulated input stages up to 900 MHz in diode-tuned tuners.

Type	Ordering code
AF 279 S	Q62701-F87



Approx. weight 0.25 g

Dimensions in mm

Maximum ratings

Collector-emitter voltage	$-V_{CEO}$	15	V
Collector-emitter voltage	$-V_{CES}$	20	V
Emitter-base voltage	$-V_{EBO}$	0.3	V
Collector current	$-I_C$	10	mA
Emitter current	I_E	11	mA
Base current	$-I_B$	1	mA
Junction temperature	T_j	90	°C
Storage temperature range	T_{stg}	-30 to +75	°C
Total power dissipation	P_{tot}	60	mW

Thermal resistance

Junction to ambient air	R_{thJA}	≤600	K/W
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Static characteristics ($T_{amb} = 25^{\circ}\text{C}$)

$-V_{CE}$ V	$-I_C$ mA	$-I_B$ μA	h_{FE} I_C/I_B	$-V_{BE}$ mV
10	2	40	50 (<10)	350
5	5	110	45	400

Collector cutoff current ($-V_{CES} = 20\text{ V}$)	$-I_{CES}$	1 (<15)	μA
Collector cutoff current ($-V_{CEO} = 15\text{ V}$)	$-I_{CEO}$	<500	μA
Emitter cutoff current ($-V_{EBO} = 0.3\text{ V}$)	$-I_{EBO}$	<100	μA

Dynamic characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Transition frequency ($-I_C = 2\text{ mA}$; $-V_{CE} = 10\text{ V}$; $f = 100\text{ MHz}$)	f_T	820	MHZ
Collector base capacitance ($-V_{CB} = 10\text{ V}$; $f = 1\text{ MHz}$)	$-C_{CB0}$	0.4	pF
Power gain ($-I_C = 2\text{ mA}$; $-V_{CE} = 10\text{ V}$; $f = 800\text{ MHz}$; $R_L = 2\text{ k}\Omega$)	G_{pb}	20	dB
($-I_C = 2\text{ mA}$; $-V_{CE} = 10\text{ V}$; $f = 900\text{ MHz}$; $R_L = 500\Omega$)	G_{pb}	12	dB
Noise figure ($-I_C = 2\text{ mA}$; $-V_{CE} = 10\text{ V}$; $f = 800\text{ MHz}$; $R_g = 60\Omega$)	NF	<4.5	dB

Four-pole characteristics:

$-I_C = 2\text{ mA}$; $-V_{CE} = 10\text{ V}$; $f = 800\text{ MHz}$ (measured at a spacing of 1.5 mm)

$g_{11b} = 23\text{ mS}$	$ y_{12b} = 0,6\text{ mS}$	$ y_{21b} = 38\text{ mS}$	$g_{22b} = 0,3\text{ mS}$
$-b_{11b} = 33\text{ mS}$	$\varphi_{12b} = -90^{\circ}$	$\varphi_{21b} = 75^{\circ}$	$b_{22b} = 2,5\text{ mS}$

Test circuit for power gain and noise figure at $f = 800\text{ MHz}$

